onsemi

High-Voltage General-Purpose Diode MMBD1401A, MMBD1403A, MMBD1404A, MMBD1405A

Description

Sourced from process 2V.

ABSOLUTE MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ (Notes 2, 3)

Rating	Symbol	Value	Unit
Working Inverse Voltage	WIV	175	V
Average Rectified Current	Ι _Ο	200	mA
DC Forward Current	١ _F	600	mA
Recurrent Peak Forward Current	İf	700	mA
Non–Repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	İf(surge)	1.0 2.0	A
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature	TJ	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 2. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ (Note 4)

Characteristic	Symbol	Value	Unit
Power Dissipation	PD	350	mW
Derate Above 25°C		2.8	mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	357	°C/W

4. Device is mounted on glass epoxy PCB 1.6 inch \times 1.6 inch \times 0.06 inch, mounting pad for the collector lead minimum 0.93 in².

ELECTRICAL CHARACTERISTICS

(T_A = 25° C unless otherwise noted)

Parameter	Symbol	Condition	Min	Max	Unit
Breakdown Voltage	B _V	I _R = 100 μA	250	I	V
Reverse Current	I _R	V _R = 120 V	-	40	nA
		V _R = 175 V	-	100	nA
Forward Voltage	VF	I _F = 10 mA	-	800	mV
		I _F = 50 mA	760	920	mV
		I _F = 200 mA	-	1.1	V
		I _F = 300 mA	-	1.25	V
Diode Capacitance	CO	$V_{R} = 0, f = 1.0 \text{ MHz}$	-	2.0	рF
Reverse Recovery Time	t _{rr}	$I_F = I_R = 30 \text{ mA},$ $I_{RR} = 3.0 \text{ mA},$ $R_L = 100 \Omega$	-	50	ns

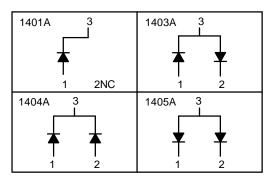
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





SOT-23 CASE 318BM SOT-23 CASE 318-08

CONNECTION DIAGRAMS



MARKING DIAGRAM



AXX = Specific Device Code XX = 29/32/33/34

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBD1404	SOT-23 (Pb-Free)	3000 / Tape & Reel

DISCONTINUED (Note 1)

MMBD1401A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBD1403A	SOT–23 (Pb–Free)	3000 / Tape & Reel
MMBD1405A	SOT–23 (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

 DISCONTINUED: These devices are not recommended for new design. Please contact your onsemi representative for information. The most current information on these devices may be available on <u>www.onsemi.com</u>.

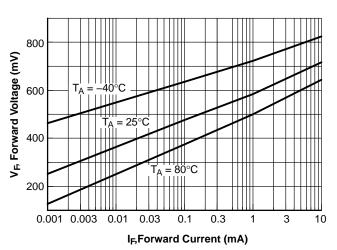
MMBD1401A, MMBD1403A, MMBD1404A, MMBD1405A

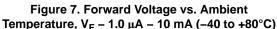
325 50 $T_A = 25°C$ $T_A = 25^{\circ}C$ 40 V_R, Reverse Voltage (V) l_R, Reverse Current (nA) 30 300 20 GENERAL RULE: The Reverse Current of a diode 10 will approximately double for every ten (10) Degree C increase in Temperature. 0 275 95 3 5 10 20 30 50 100 55 75 115 135 155 175 195 I_R, Reverse Current (µA) V_R, Reverse Voltage (V) Figure 1. Reverse Voltage vs. Reverse Current Figure 2. Reverse Current vs. Reverse Voltage $B_V - 1.0$ to 100 μA I_R – 55 to 205 V 100 $T_A = 25^{\circ}C$ $T_A = 25^{\circ}C$ 450 90 GENERAL RULE: The Reverse Current of a diode V_F, Forward Voltage (mV) l_R, Reverse Current (nA) will approximately double for every ten Degree C 80 400 increase in Temperature. 70 60 350 50 300 40 30 250 20 ĭ80 200 220 240 255 2 3 5 10 20 30 50 100 V_R, Reverse Voltage (V) I_F, Forward Current (μA) Figure 3. Reverse Current vs. Reverse Voltage Figure 4. Forward Voltage vs. Forward Current I_R - 180 to 255 V $V_{F} - 1.0$ to 100 μ A 725 1.4 $T_A = 25^{\circ}C$ $T_A = 25^{\circ}C$ 700 1.3 V_F, Forward Voltage (mV) V_F, Forward Voltage (mV) 650 1.2 1.1 600 1.0 550 0.9 500 0.8 450 <u>–</u> 0.1 0.7 0.2 0.3 0.5 1 2 3 5 10 10 20 30 50 100 200 300 500 800 IF, Forward Current (mA) IF, Forward Current (mA) Figure 5. Forward Voltage vs. Forward Current Figure 6. Forward Voltage vs. Forward Current V_F - 0.1 to 10 mA V_F - 10 to 800 mA

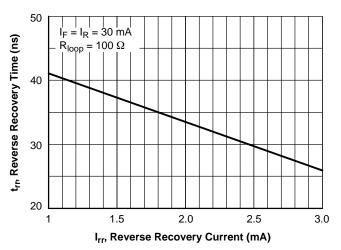
TYPICAL CHARACTERISTICS

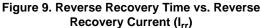
MMBD1401A, MMBD1403A, MMBD1404A, MMBD1405A

TYPICAL CHARACTERISTICS (Continued)









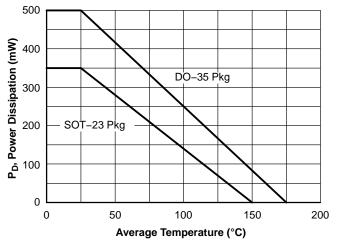
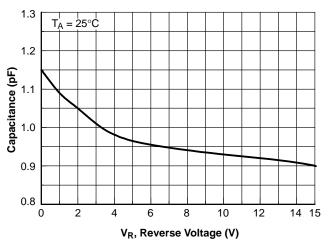
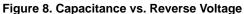


Figure 11. Power Derating Curve





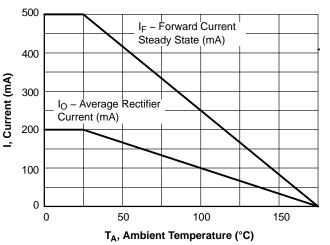


Figure 10. Average Rectified Current (I_O) and Forward Current (I_F) vs. Ambient Temperature (T_A)



semi



SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

ISSUE AU

DATE 14 AUG 2024













XXX = Specific Device Code М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MILLIMETERS						
DIM	MIN	NOM	МАХ			
А	0.89	1.00	1.11			
A1	0.01	0.06	0.10			
b	0.37	0.44	0.50			
с	0.08	0.14	0.20			
D	2.80	2.90	3.04			
E	1.20	1.30	1.40			
е	1.78	1.90	2.04			
L	0.30	0.43	0.55			
L1	0.35	0.54	0.69			
Ηe	2.10	2.40	2.64			
Т	0°		10°			

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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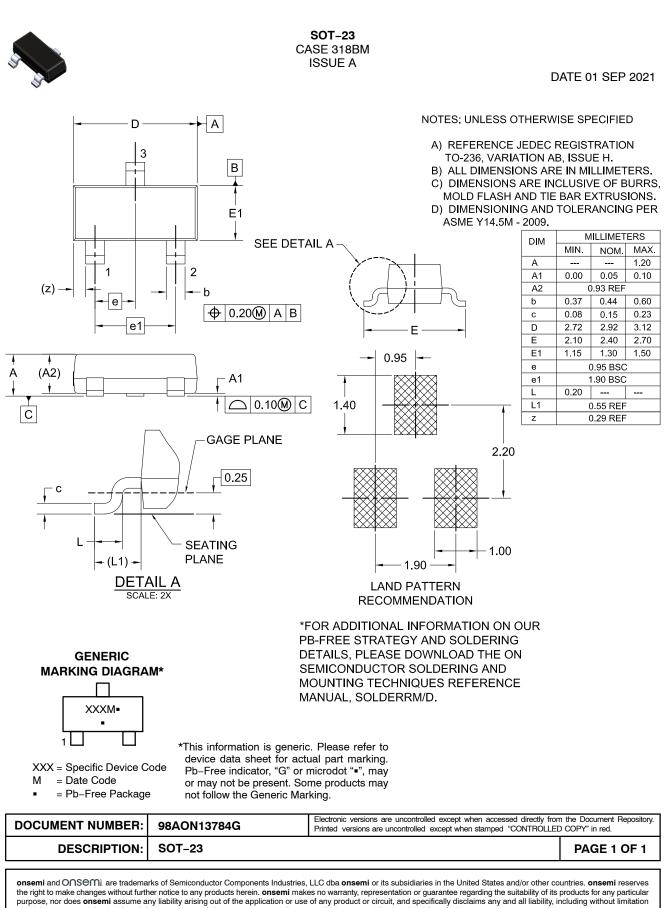
DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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